

Application No.: 10/669940
Docket No.: CL2173USNA

Page 2

AMENDMENTS TO CLAIMS

Claims 1-13 (Cancelled).

14. (Currently Amended) A transistor comprising a an undoped, transparent, metal oxide semiconductor component comprising an undoped transparent metal oxide electrically coupled between a source electrode and a drain electrode, and a gate electrode electrically coupled to said undoped transparent metal oxide semiconductor, such that the application of a bias to the gate electrode controls electric current flow in the undoped transparent metal oxide semiconductor between source and drain electrodes.
15. (Cancelled).
16. (Currently Amended) A flat panel display comprising one or an array of transparent oxide semiconductor transistors as described by as recited in Claim 14.
17. (Currently Amended) An active matrix imager comprising an array of transparent oxide semiconductor transistors as described by as recited in Claim 14.
18. (Currently Amended) A sensor comprising an array of transparent oxide semiconductor transistors as described by as recited in Claim 14.
19. (Currently Amended) A rf price label comprising an array of transparent oxide semiconductor transistors as described by as recited in Claim 14.
20. (Currently Amended) A rf identification tag comprising an array of transparent oxide semiconductor transistors as described by as recited in Claim 14.
21. (Currently Amended) A rf inventory tag comprising an array of transparent oxide semiconductor transistors as described by as recited in Claim 14.
22. (Currently amended) The transistor of Claim 14 deposited on a flexible substrate .
23. (Currently amended) The transistor of Claim 14 further comprising a gate electrode, and wherein said source, drain and gate electrodes are fabricated from a material selected from the group consisting of zinc oxide, indium oxide, tin oxide, and cadmium oxide.
24. (Original) The transistor of Claim 22 further comprising a gate dielectric fabricated from a material selected from the group consisting of zinc oxide, indium oxide, tin oxide, and cadmium oxide.
25. (New) The transistor of claim 14 wherein said updoped, transparent metal oxide semiconductor comprises at least one oxide selected from: zinc oxide, indium oxide, tin oxide, and cadmium oxide.